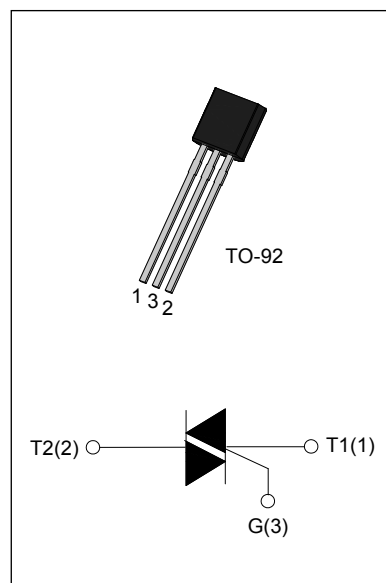




DESCRIPTION:

With low holding and latching current, JST132 series triacs are especially recommended for use on middle and small resistance type power load. Package TO-92 is RoHS compliant.
(2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	0.5	A
V_{DRM} / V_{RRM}	600/800	V
V_{TM}	1.65	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40 - 150	°C
Operating junction temperature range	T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600/800	V
RMS on-state current TO-92 ($T_C=50^\circ\text{C}$)	$I_{T(RMS)}$	0.5	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	5	A
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	0.18	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	10	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	0.2	A
Average gate power dissipation	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	0.5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V}$	I - II - III	MAX	5	mA
		IV		10	
V_{GT}		ALL	MAX	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX	10	mA
		II		15	
I_H	$I_T=100\text{mA}$		MAX	10	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	15	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=1.1\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.65	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	100	μA

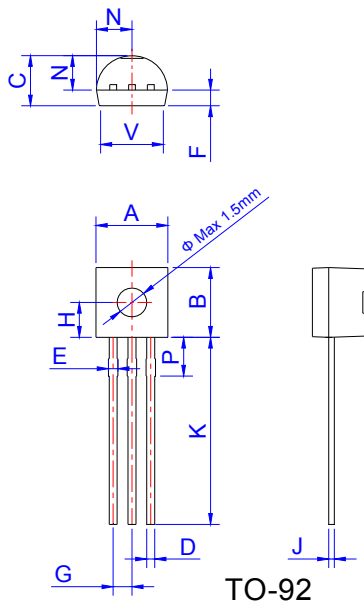
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-92	113	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

<p>J</p> <p>JieJie Microelectronics Co.,Ltd</p>	<p>ST</p> <p>TRIACs</p>	<p>132</p> <p>$I_{T(RMS)}:0.5\text{A}$</p>	<p>U</p> <p>U:TO-92</p>	<p>-600</p> <p>600:$V_{DRM}/V_{RRM}\geq 600\text{V}$ 800:$V_{DRM}/V_{RRM}\geq 800\text{V}$</p>	<p>D</p> <p>D:$I_{GT1-3}\leq 5\text{mA}$ $I_{GT4}\leq 10\text{mA}$</p>
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PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

PACKAGE INFORMATION

PACKAGE	WEIGHT (PER PCS)	OUTLINE	BAG (PCS)	INNER BOX (PCS)	PER CARTON
TO-92	0.1894g	Shielding Bag	1,000	10,000	30,000
TO-92	0.1894g	Shielding Bag	1,000	10,000	50,000
TO-92	0.1894g	Shielding Bag	1,000	10,000	100,000

FIG.1: Maximum power dissipation versus RMS on-state current

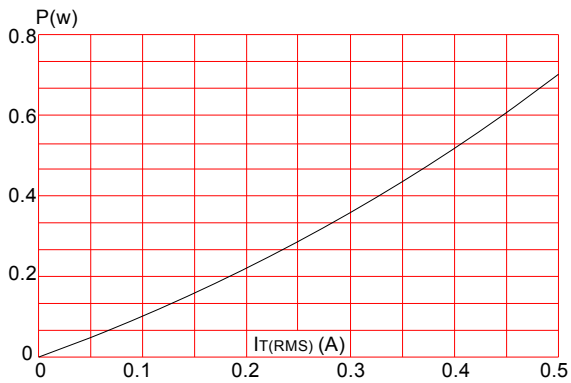


FIG.2: RMS on-state current versus case temperature

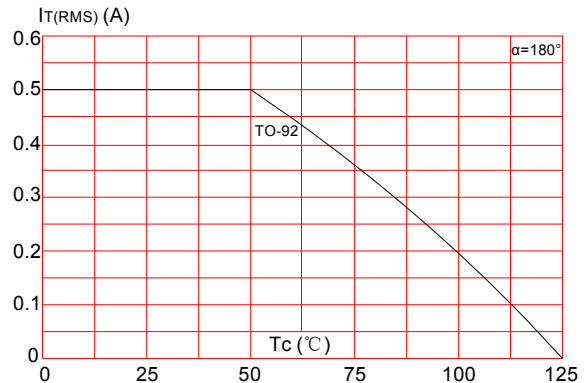


FIG.3: Surge peak on-state current versus number of cycles

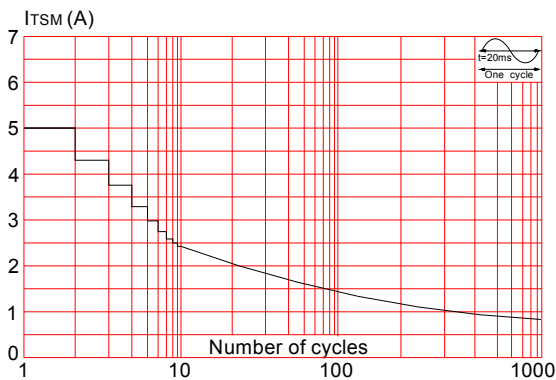


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ ($di/dt < 10\text{A}/\mu\text{s}$)

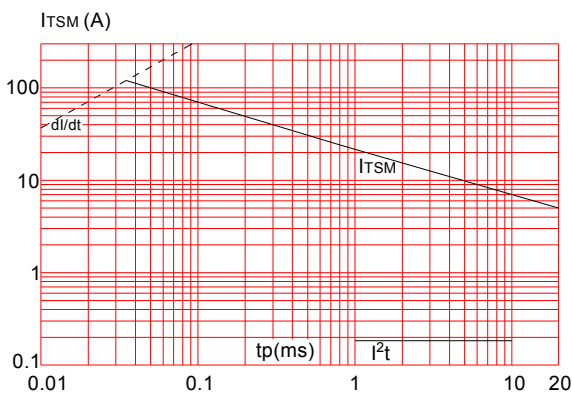


FIG.4: On-state characteristics (maximum values)

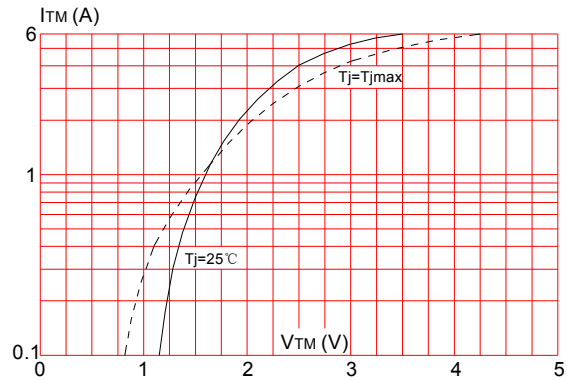
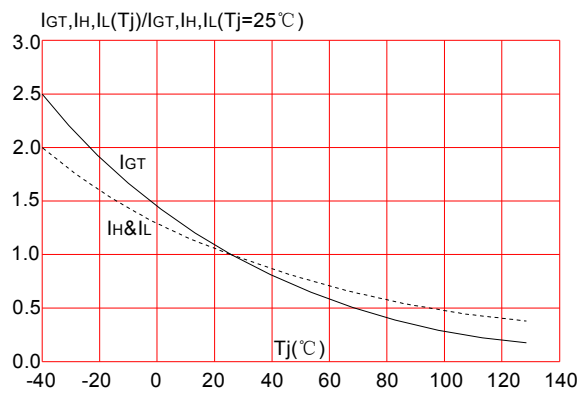



FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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